

ABSTRACT OF THE DISCLOSURE

5       A column select gate in a ferroelectric memory is constituted by only P-channel MOS transistors. While a column select signal is set to low level, and a data line is set to 0 V, data is read out from a memory cell to a bit line. A potential amplified and held by a sense amplifier is transferred to the data line through the current path of the column select gate formed from the P-channel MOS transistors.